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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	09/945554
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Dickey, Thomas

Attorney Docket No: 1303.028US1

Sheet 1 of 2

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
Tb	US-5,952,692	09/14/1999	Nakazato, K. , et al.	257	321	10/28/1997
Tb	US-6,210,999	04/03/2001	Gardner, , et al.	438	183	12/04/1998
Tb	US-6,475,857	11/05/2002	Kim, W. , et al.	438	240	06/21/2001
Tb	US-6,541,280	04/01/2003	Kaushik, , et al.			03/20/2001

**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>3</sup>
Tb		AARIK, JAAN , et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", <u>Journal of Crystal Growth</u> , (2000), pp. 531-537	
Tb		AARIK, JAAN , et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , (2000), pp. 105-113	
Tb		FERGUSON, J D., et al., "Atomic layer deposition of Al <sub>2</sub> O <sub>3</sub> and SiO <sub>2</sub> on BN particles using sequential surface reaction", <u>Applied Surface Science</u> , (2000), pp. 280-292	
Tb		KIM, YONG S., et al., "Effect of rapid thermal annealing on the structure and the electrical properties of atomic-layer-deposited Ta <sub>2</sub> O <sub>5</sub> films", <u>Journal of the Korean Physical Society</u> , (December 2000), pp. 975-979	
Tb		KIM, YEONG K., et al., "Novel capacitor technology for high density stand-alone and embedded DRAMs", <u>IEEE</u> , (2000), 4 pages	
Tb		KUKLI, KAUPO , "Atomic Layer Deposition of Titanium Oxide from TiI <sub>4</sub> and H <sub>2</sub> O <sub>2</sub> ", <u>Chemical Vapor Deposition</u> , (2000), pp. 303-310	
Tb		KUKLI, KAUPO , et al., "Atomic layer deposition of zirconium oxide from zirconium tetraiodide, water and hydrogen peroxide", <u>Journal of Crystal Growth</u> , (2001), pp. 262-272	
Tb		KUKLI, KAUPO , et al., "Real-time monitoring in atomic layer deposition of TiO <sub>2</sub> from TiI <sub>4</sub> and H <sub>2</sub> O-H <sub>2</sub> O <sub>2</sub> ", <u>American Chemical Society</u> , (2000), pp. 8122-8128	
Tb		LEE, J. , "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-Al <sub>2</sub> O <sub>3</sub> Gate Dielectric", <u>IEDM</u> , (2000), pp. 645-648	
Tb		PARANJPE, AJIT , et al., "Atomic layer deposition of AlO <sub>x</sub> for thin film head gap application", <u>Journal of the Electrochemical Society</u> , (September 2001), pp. 465-471	

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\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Examiner Name	Dickey, Thomas

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